SOD-523 Schottky Barrier Rectifier Diode 肖特基势垒整流二极管

■Features 特点

Low forward voltage drop 低正向压降
High current capability 高电流能力
Surface mount device 表面贴装器件
Case 封装:SOD-523

■Maximum Rating 最大额定值

(T_A=25℃ unless otherWTise noted 如无特殊说明，温度为 25℃)

Characteristic 特性参数	Symbol 符号	B5817WT	B5818WT	B5819WT	Unit 单位
Device Marking 产品印字		SJ	SK	SL	
Peak Reverse Voltage 反向峰值电压	V_{RRM}	20	30	40	V
DC Reverse Voltage 直流反向电压	V_R	20	30	40	V
RMS Reverse Voltage 反向电压均方根值	V_{RMS}	14	21	28	V
ForWTard Rectified Current 正向整流电流	I_F	1			A
Peak Surge Current 峰值浪涌电流	I_{FSM}	5			A
PoWTer Dissipation 耗散功率	P_D	250			mW
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	400			℃/W
Junction/Storage Temperature 结温/储藏温度	T_J,T_{stg}	-50to+125℃			℃

■Electrical Characteristics 电特性

(T_A=25℃ unless otherWTise noted 如无特殊说明，温度为 25℃)

Characteristic 特性参数	Symbol 符号	B5817WT	B5818WT	B5819WT	Unit 单位	Condition 条件
Reverse Voltage 反向电压	V_R	20	30	40	V	I_R=1mA
ForWTard Voltage 正向电压	V_F	0.45	0.55	0.6	V	I_F=1A
Reverse Current 反向电流	I_R	1			mA	V_R=V_{RRM}
Diode Capacitance 二极管电容	C_T	120			pF	V_R=4V,f=1MHz

■Typical Characteristic Curve 典型特性曲线

Fig.1 Power Derating Curve

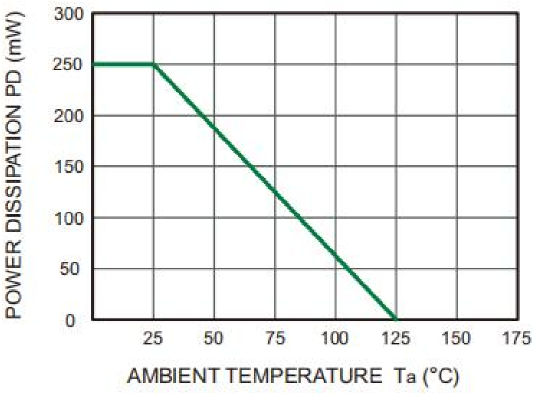


Fig.2 Typical Reverse Characteristics

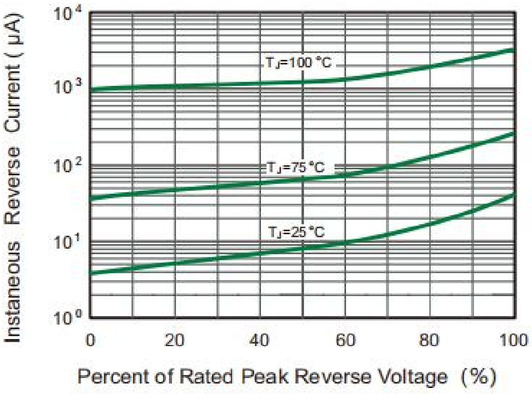


Fig.3 TYPICAL FORWARD VOLTAGE

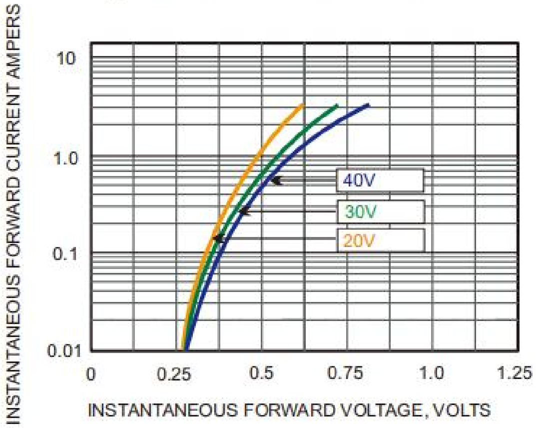
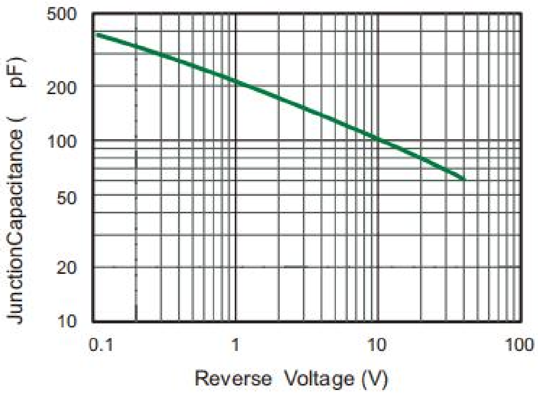
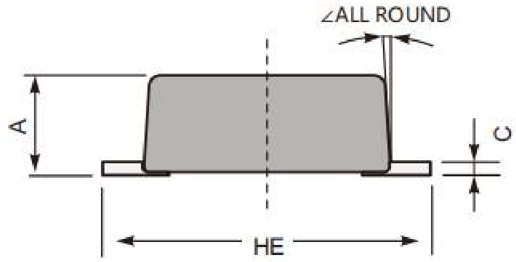
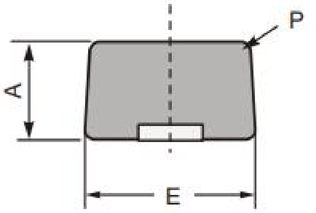


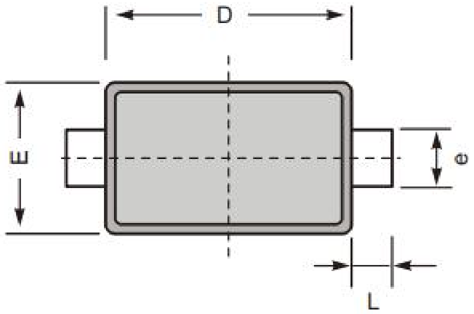
Fig.4 Typical Junction Capacitance

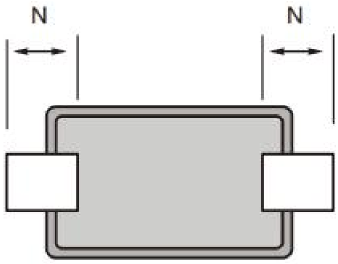


■ Dimension 外形封装尺寸









底视图
bottom view

UNIT		A	e	C	D	E	HE	N	L	P	∠
mm	max	0.77	0.35	0.15	1.30	0.99	1.70	0.35 ref	0.2 ref	R0.1 ALL ROUND	10° ±1°
	min	0.51	0.25	0.08	1.10	0.75	1.50				
mil	max	30	14	6	51	39	67	14 ref	8.0 ref	R4.0 ALL ROUND	
	min	20	10	3	43	30	59				